

# Jin Onuki

## List of Publications by Year in descending order

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19  
papers

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citations

1937685

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2053705

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times ranked

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#	ARTICLE	IF	CITATIONS
1	Reliability Enhancement of Thick Al&ndash;Cu Wire Bonds in IGBT Modules Using Al<sub>2</sub>O<sub>3</sub>/Cu Precipitates. Materials Transactions, 2012, 53, 453-456.	1.2	6
2	Determination of the Phase-Field Parameters for Computer Simulation of Heat Treatment Process of Ultra Thin Al Film. Materials Transactions, 2007, 48, 1998-2001.	1.2	5
3	Improvement of the Surface Layer of Steel Using Microwave Plasma Nitriding. Materials Transactions, 2004, 45, 942-946.	1.2	4
4	Computer Simulation of Silicon Nanoscratch Test. Materials Transactions, 2006, 47, 1090-1097.	1.2	4
5	Development of the High-Speed Plating Technology of Through-Electrodes for the Three Dimensional Packaging. Journal of Japan Institute of Electronics Packaging, 2010, 13, 213-219.	0.1	4
6	High-Temperature Cycle Durability of Superplastic Al&dash;Zn Eutectoid Solder Joints With Stress Relaxation Characteristics for SiC Power Semiconductor Devices. IEEE Electron Device Letters, 2019, 40, 303-306.	3.9	3
7	Microwave Plasma Nitriding of Hollow Tube Inner Wall. Materials Transactions, 2004, 45, 599-601.	1.2	2
8	Development of Damage Free Thick Al-Cu Wire Bonding Process and Reliability of the Wire Bonds. Electrochemistry, 2014, 82, 100-103.	1.4	2
9	Beam Characterization for Scanning Electron Microscopes by the RPS and IPC Methods. Microscopy and Microanalysis, 2015, 21, 54-59.	0.4	2
10	Investigation on Microstructure and Resistivity in Cu-TSVs for 3D Packaging. Transactions of the Japan Institute of Electronics Packaging, 2016, 9, E16-010-1-E16-010-7.	0.4	2
11	Grain Size Distribution at the Bottom Region in Very Narrow Cu Interconnects. Electrochemistry, 2016, 84, 151-155.	1.4	2
12	Highly reliable high-temperature superplastic Al-Zn eutectoid solder joining with stress relaxation characteristics for next generation SiC power semiconductor devices. , 2017, , .		2
13	Nano-Structure-Controlled Very Low Resistivity Cu Wires Formed by High Purity and Optimized Additives. IEEE Journal of the Electron Devices Society, 2018, 6, 506-511.	2.1	2
14	Effects of Electroplating at Lower Leveler and Suppressor Contents on the Formation of Very Low Resistivity Narrow Cu Interconnects. Journal of the Electrochemical Society, 2019, 166, D137-D143.	2.9	2
15	Phase field simulation of heat treatment process of Cu ultra fine wire. Transactions of the Materials Research Society of Japan, 2008, 33, 237-239.	0.2	2
16	Nanoscratching of Metallic Thin Films on Silicon Substrate: a Molecular Dynamics Study. Journal of Electronic Materials, 2007, 36, 1174-1180.	2.2	1
17	Reduction of Plating Time for Through Silicon Via (TSV) by High-Speed Solution Flow Plating Method and Texture Investigation of the TSV. Journal of Japan Institute of Electronics Packaging, 2011, 14, 513-518.	0.1	1
18	Investigation on microstructure and resistivity in Cu-TSVs for 3D packaging. , 2016, , .		1

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19	Nano-structure-controlled very low resistivity Cu wires formed by high purity electrolyte and optimized additives. , 2017, , .		0